AO1122

ZERO-DRIFT, RAIL-TO-RAIL SINGLE I/O CMOS OP AMPLIFIER

DESCRIPTION

The AO1122 is single CMOS operational amplifier use auto-zero techniques to simultaneously provide very low offset voltage ($5\mu V$ Max) and near-zero drift over time and temperature.

This AO1122 amplifier has ultralow noise, offset and power

This AO1122 miniature, high-precision operational amplifier offset high input impedance and rail-to-rail input and rail-to-rail output swing. With high gain-bandwidth product of 350KHz and slew rate of 0.17V/µs.

Single or dual supplies as low as +2.3V ($\pm 1.15V$) and up to +5.5V ($\pm 2.75V$) may be used.

The AO1122 is available in SOT-25 and SOP8, MSOP8 package.

ORDERING INFORMATION

Package Type	Part Number		
SOT-25	E5	AO1122E5R	
SPQ: 3,000pcs/Reel	E3	AO1122E5VR	
SOP8	MO	AO1122M8R	
SPQ: 4,000pcs/Reel	M8	AO1122M8VR	
MSOP8	MS8	AO1122MS8R	
SPQ: 4,000pcs/Reel	IVISO	AO1122MS8VR	
Note	V: Halogen free Package		
note	R: Tape & Reel		
AiT provides all RoHS products			

FEATURES

Low Offset Voltage: 1uV(TYP.)

■ Input Offset Drift: ±0.005µV/°C

High Gain Bandwidth Product: 350KHz

Rail-to-Rail Input and Output

High Gain, CMRR, PSRR:130dB

High Slew Rate: 0.17V/μs

• Low Noise: 3.2uVp-p (0.01~10Hz)

Low Power Consumption: 60μA /op amp

Overload Recovery Time:6us

Low Supply Voltage: 2.3 V to 5.5 V

No External Capacitors Required

Extended Temperature: -40°C ~ +125°C

APPLICATION

Temperature Sensors

Medical/Industrial Instrumentation

Pressure Sensors

Battery-Powered Instrumentation

Active Filtering

Weight Scale Sensor

Strain Gage Amplifiers

Power Converter/Inverter

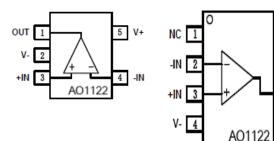
TYPICAL APPLICATION

SOT-25 SOP8/MSOP8

NC

OUT

NC

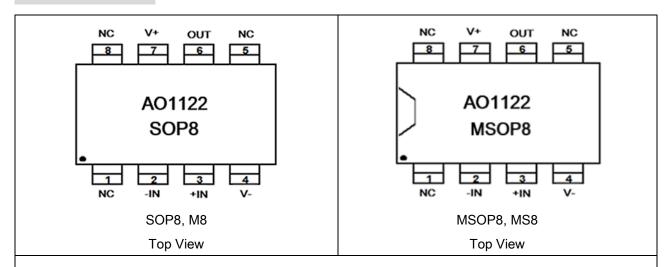


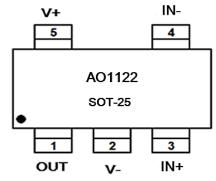
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PIN DESCRIPTION





SOT-25, E5 Top View

	PIN#		Cumhal	Function
SOP8	MSOP8	SOT-25	Symbol	Function
6	6	1	OUT A	Output
4	4	2	-IN A Negative (Lowest) Power Supply	
3	3	3	+IN A Positive (Noninverting) Input	
2	2	4	V- Negative (Inverting) Input	
7	7	5	+IN B Positive (Highest) Power Supply	
1,3,5	1,3,5		-IN B No Internal Connection (can be Left Floati	

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AO1122

ZERO-DRIFT, RAIL-TO-RAIL SINGLE I/O CMOS OP AMPLIFIER

ABSOLUTE MAXIMUM RATINGS

V _S , Supply, V _S =(V+) - (V-), Voltage		7.0V
Signal Input Pin, Voltage(1)		(V-)-0.5 to (V+)0.5V
Signal Output Pin, Voltage(2)		(V-)-0.5 to (V+)0.5V
Signal Input Pin, Current ⁽¹⁾		±10mA
Signal Output Pin, Current(2)		±55mA
Output Short-Circuit, Current(3)		Continuous
	SOP8	110°C/W
θ _{JA} , Package Thermal Impedance ⁽⁴⁾	MSOP8	170°C/W
	SOT-25	230°C/W
T _A , Operating Range		-40°C ∼ +125°C
T _{STG} , Storage Temperature		-65°C ~ +150°C
T _J , Junction Temperature ⁽⁵⁾		-40°C ∼ +150°C
ESD Ratings		
Vanna Electrostatic Discharge	Human-Body Model (HBM)	±5000V
V _(ESD) , Electrostatic Discharge	Machine Model (MM)	±400V

^{*}Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied.

- (1) Input terminals are diode-clamped to the power-supply rails. Input signals that can swing more than 0.5V beyond the supply rails should be current-limited to 10mA or less.
- (2) Output terminals are diode-clamped to the power-supply rails. Output signals that can swing more than 0.5V beyond the supply rails should be current-limited to ±55mA or less.
- (3) Short-circuit to ground, one amplifier per package.
- (4) The package thermal impedance is calculated in accordance with JESD-51.
- (5) The maximum power dissipation is a function of $T_{J \text{ (MAX)}}$, $R_{\theta JA}$, and T_{A} . The maximum allowable power dissipation at any ambient temperature is PD = $(T_{J \text{ (MAX)}} T_{A}) / R_{\theta JA}$. All numbers apply for packages soldered directly onto a PCB.

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Conditions	Min	Тур.	Max	Unit
Supply Voltage	V _S =(V+) - (V-)	Single-Supply	2.3	-	5.5	V
		Dual-Supply	±1.15		±2.75	

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ELECTRICAL CHARACTERISTICS

At $T_A = +25^{\circ}C$, $V_S=5V$, $R_L = 10k\Omega$ connected to $V_S/2$, and $V_{OUT} = V_S/2$, unless otherwise noted.

Parameter	Symbol	Conditions	Min	Typ.	Max	Unit
OFFSET VOLTAGE				- 7		
Input Offset Voltage	Vos	$V_{CM} = V_S/2$	-5	±1	5	μV
Input Offset Voltage Average Drift	Vos Tc	V CIVI V 37 Z		±0.005	±0.05	μV/°C
Power-Supply Rejection Ratio	PSRR	V _S =2.3V to 5.5V, V _{CM} = 0	110	130		dB
Channel Separation		VS-2.3V to 3.3V, VCM - 0			-	μV/V
·	dc		-	0.1	-	μν/ν
INPUT BIAS CURRENT	1	\/ -\/ ₂ /2		140	l e	Λ
Input Bias Current(1)(2)	I _B	$V_{CM} = V_S/2$	-	±10	-	pΑ
Input Offset Current(1)	los		-	±10	_	pA
NOISE PERFORMANCE		6 0 0411 / 4011			Ī	
Input Voltage Noise	e _n p-p	f=0.01Hz to 10Hz	-	3.2	-	μVpp
	' '	f=0.01Hz to 1Hz	-	0.97	-	μVpp
Input Voltage Noise Density	e n	f=1KHz	-	140	-	nV/√Hz
Input Current Noise Density	İn	f=10Hz	-	15	-	fA/√Hz
INPUT VOLTAGE RANGE					T	
Common-Mode Voltage Range	Vсм		-0.1	-	0.1	V
Common-Mode Rejection Ratio	CMRR	$(V-)-0.1V < V_{CM} < (V+) + 0.1V$	110	130	-	dB
INPUT CAPACITANCE						
Differential			-	1	-	pF
Common-Mode			-	5	-	pF
OPEN-LOOP GAIN						
	Aol	$R_L=10K\Omega$, $V_O=0.3V \sim 4.7V$,		400		
Open-Loop Voltage Gain		T _A = -40°C ~ +125°C	110	130	-	dB
DYNAMIC PERFORMANCE						
Slew Rate ⁽⁵⁾	SR	G=+1	-	0.17	_	V/µs
Gain-Bandwidth Product	GBW		-	350	_	KHz
Overload Recovery Time	tor		-	6	_	us
OUTPUT CHARACTERISTICS	•010					3.5
	V _{OH}	R _L =100 KΩ to GND	4.99	4.998	_	V
Output Voltage High		R _L =10KΩ to GND	4.95	4.98	-	V
Output Voltage Low	V _{OL}	RL=100 KΩ to V+	1	1	10	mV
		RL=10 KΩ to V+		10	30	mV
Short-Circuit Current(3)(4)	I _{SC}		-	25	_	mA
POWER SUPPLY						
Operating Voltage Range	Vs		2.3	-	5.5	V
Quiescent Current/Amplifier	IQ		-	60	87	μA

⁽¹⁾ This parameter is ensured by design and/or characterization and is not tested in production.

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⁽²⁾ Positive current corresponds to current flowing into the device.

⁽³⁾ The maximum power dissipation is a function of $T_{J \text{ (MAX)}}$, $R_{\theta JA}$, and T_{A} . The maximum allowable power dissipation at any ambient temperature is PD = $(T_{J \text{ (MAX)}} - T_{A}) / R_{\theta JA}$. All numbers apply for packages soldered directly onto a PCB.

⁽⁴⁾ Short circuit test is a momentary test.

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(5) Number specified is the slower of positive and negative slew rates.

TYPICAL PERFORMANCE CHARACTERISTICS

Fig 1. Offset Voltage Production Distribution

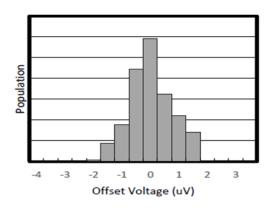


Fig 2. Offset Voltage Production Distribution

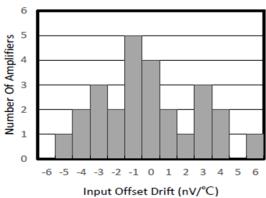


Fig 3. Open-Loop Gain and Phase vs. Frequency

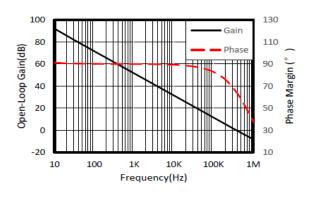


Fig 4. Input Bias Current vs. Temperature

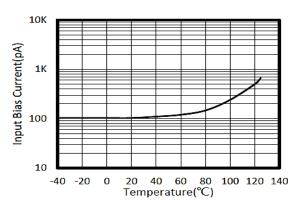


Fig 5. Power-Supply Rejection Ratio vs. Frequency

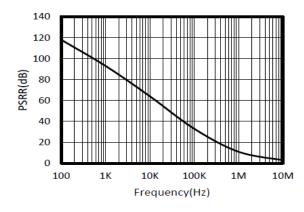
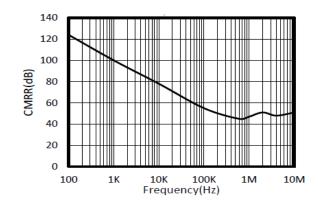
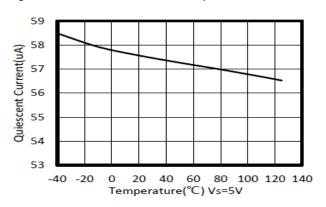


Fig 6. Common-Mode Rejection Ratio vs. Frequency



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Fig 8. Quiescent Current vs. Temperature

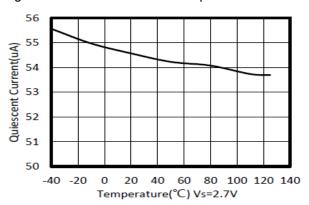


Fig 9. Sink Current vs. Temperature

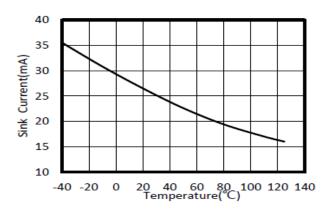


Fig 10. Source Current vs. Temperature

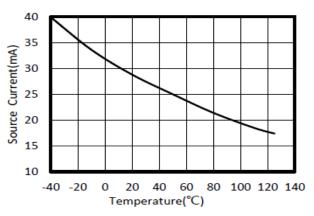


Fig 11. Small-Signal Step Response

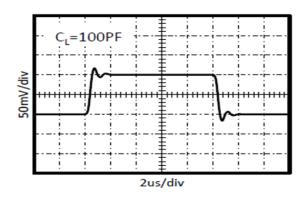
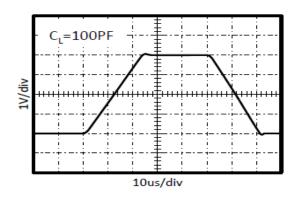


Fig 12. Large-Signal Step Response



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Fig 13. Positive Overvoltage Recovery

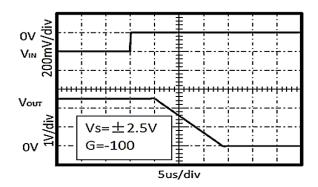


Fig 15. 0.01Hz to 10Hz Noise at V_S =5V

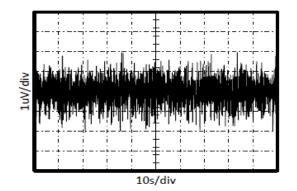


Fig 17. 0.01Hz to 1Hz Noise at V_S=5V

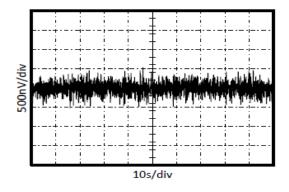


Fig 14. Negative Overvoltage Recovery

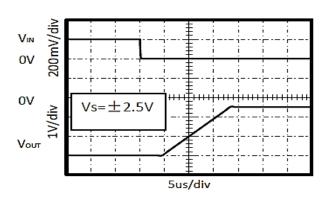


Fig 16. 0.01Hz to 10Hz Noise at V_S =2.7V

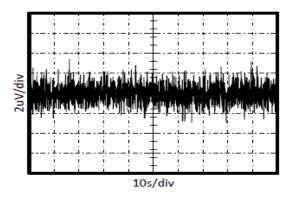
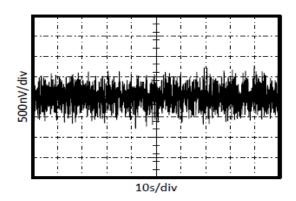


Fig 18. 0.01Hz to 1Hz Noise at V_S =2.7V

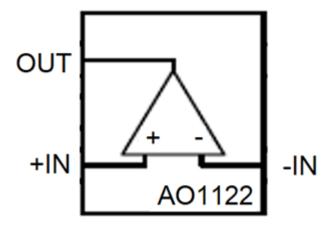


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BLOCK DIAGRAM



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DETAILED INFORMATION

Application Notes

The AO1122 is unity-gain stable and free from unexpected output phase reversal op amp. It use auto-zeroing techniques to provide low offset voltage and very low drift over time and temperature. Good layout practice mandates use of a $0.1\mu F$ capacitor practice mandates use of a $0.1\mu F$ capacitor placed closely across the supply pins.

For lowest offset voltage and precision performance, circuit layout and mechanical conditions should be optimized. Avoid temperature gradients that create thermoelectric (See beck) effects in thermocouple junctions formed form connecting dissimilar conductor. These thermally-generated potentials can be made to cancel by assuring that they are equal on both input terminals.

- Use Low Thermoelectric-Coefficient Connections (avoid dissimilar metals).
- Thermally Isolate Components Form Power Supplies or other Heat-Sources
- Shield Op Amp and input Circuitry form Air Currents, such as cooling fans.

Following these guidelines will reduce the likelihood of junctions being at different temperatures, which can cause thermoelectric voltages of $0.1\mu\text{V}/^{\circ}\text{C}$ or higher, depending on materials used.

Operating Voltage

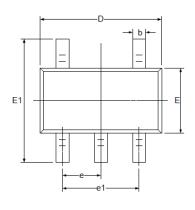
The AO1122 operates over a power-supply range of 2.3V to +5.5V (±1.15V to ±2.75V). Supply voltages higher than 7V (absolute maximum) can permanently damage the amplifier.

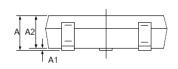
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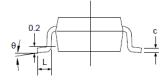
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PACKAGE INFORMATION

Dimension in SOT-25(Unit: mm)





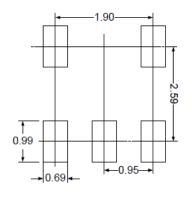


TOP VIEW

BOTTOM VIEW

SIDE VIEW

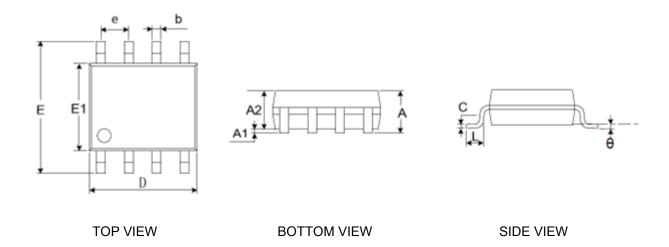
Recommended Land Pattern



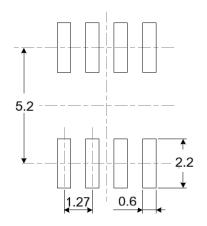
Cymbol	Millimeters				
Symbol	Min	Max			
Α	1.050	1.250			
A1	0.000	0.100			
A2	1.050	1.150			
b	0.300	0.500			
С	0.100	0.200			
D	2.820	3.020			
Е	1.500	1.700			
E1	2.650	2.950			
е	0.950 BSC				
e1	1.800	2.00			
L	0.300 0.600				
θ	0°	8°			

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Dimension in SOP8 (Unit: mm)



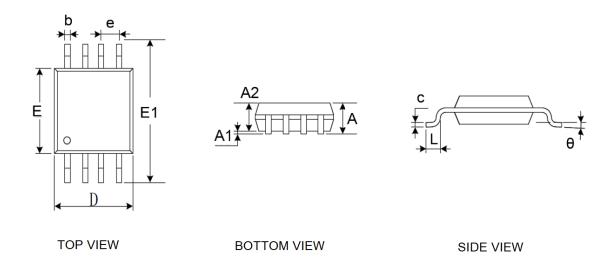
Recommended Land Pattern



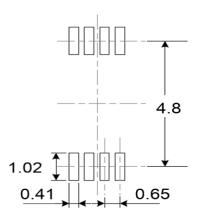
Comple of	Millimeters			
Symbol	Min	Max		
Α	1.350	1.750		
A1	0.100	0.250		
A2	1.350	1.550		
b	0.330	0.510		
С	0.170	0.250		
D	4.800	5.000		
е	1.270 BSC			
E	5.800	6.200		
E1	3.800	4.000		
L	0.400	1.270		
θ	0° 8°			

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Dimension in MSOP8 (Unit: mm)



Recommended Land Pattern



Symbol	Millimeters			
Symbol	Min	Max		
Α	0.820	1.100		
A1	0.020	0.150		
A2	0.750	0.950		
b	0.250	0.380		
С	0.090	0.230		
D	2.900	3.100		
е	0.650 BSC			
E	2.900	3.100		
E1	4.750	5.050		
L	0.400	0.800		
θ	0°	6°		

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